Zetta eMMC Product Family
eMMC Specification

Contents

1. INTRODUCTION

ZETTA eMMC is an embedded storage solution designed in the BGA package. The ZETTA eMMC consists of NAND flash and eMMC controller. The controller could manage the interface protocols, wearleveling, bad block management and ECC.

ZETTA eMMC has high performance at a competitive cost, high quality and low power consumption, and eMMC is compatible with JEDEC standard eMMC 5.1 specifications.

2. General Description

ZETTA eMMC has high performance, low power consumption features and supports eMMC4.5, eMMC5.01 and eMMC5.1 specifications. Product has single channel high speed flash interface with strong error correction code (ECC).

2.1 Product list

Capacities	Part Number	Flash Type	User Density	Package Size (mm)	Package Type
16GB	ZDEMDCM016G-84A8	256Gb TLCx1	90 %	11.5x13x1.0	153FBGA
32GB	ZDEMDCM032G-84A8	256Gb TLCx1	90 %	11.5x13x1.0	153FBGA
64GB	ZDEMDCM064G-95A8	512Gb TLCx1	90 %	11.5x13x1.0	153FBGA

Table 2-1 eMMC product list

2.2. Feature

. eMMC interface supports 1.8V/3.3V voltage

. Fully compatible with eMMC standard specification v4.5/v5.01/v5.1

- Support Bus Speed Mode: Backward compatibility for legacy MMC card mode, High Speed SDR/DDR, HS200 and HS400
- Support command class 0, 2, 4, 5, 6, 7, 8, 9, 10 and 11
- Support RPMB security engine

· eMMC interface with programmable output drive capability

. Flash interface support:

- Up to 4 flash chip selection and 8-bit flash I/O access
- Support 1.2V/1.8V flash interface
  - Asynchronous mode: 50MB/s
  - Synchronous mode: 533MB/s
- Supports both 1.2V and 1.8V flash IO voltage
- Supports both 2.5V and 3.3V flash core voltage

. Flash memory support:

- Support ECC function to correct up to 4K BCH405 with hard decoding and 4K BCH945 with soft decoding

- Support MLC/TLC/QLC NAND type flash

- Support flash with 4KB/8KB/16KB/32KB page architecture

- Support four-plane operation for 16KB page and two-plane operation for 32KB page

- Support Toggle Mode flash

- Support ONFI3.1/ONFI2.3/ONFI2.2/ONFI2.1/ONFI2.0 flash

Temperature

- Operation (-25℃ ~+85℃)

- Storage without operation (-40℃ ~+85℃)

. Low power consumption

. Enhanced ESD design

. Non-Direct remap architecture

. Manufacturing utility ready

3. eMMC Function Block Diagram

The internal block diagram is shown in the following.
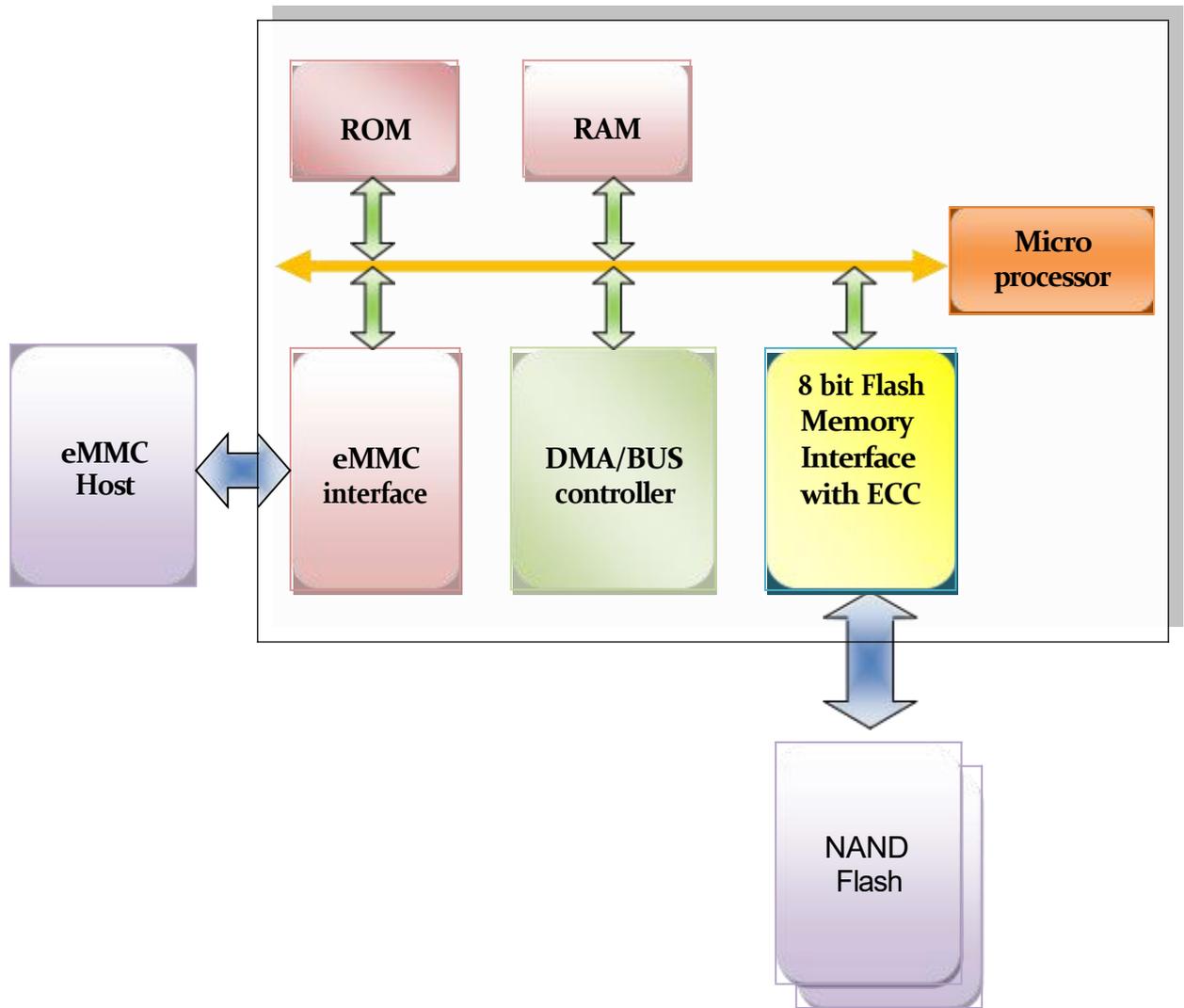
Figure 3-1 eMMC Function Block Diagram

4. Pin Description

4.1. eMMC 153 Ball Pin Assignment
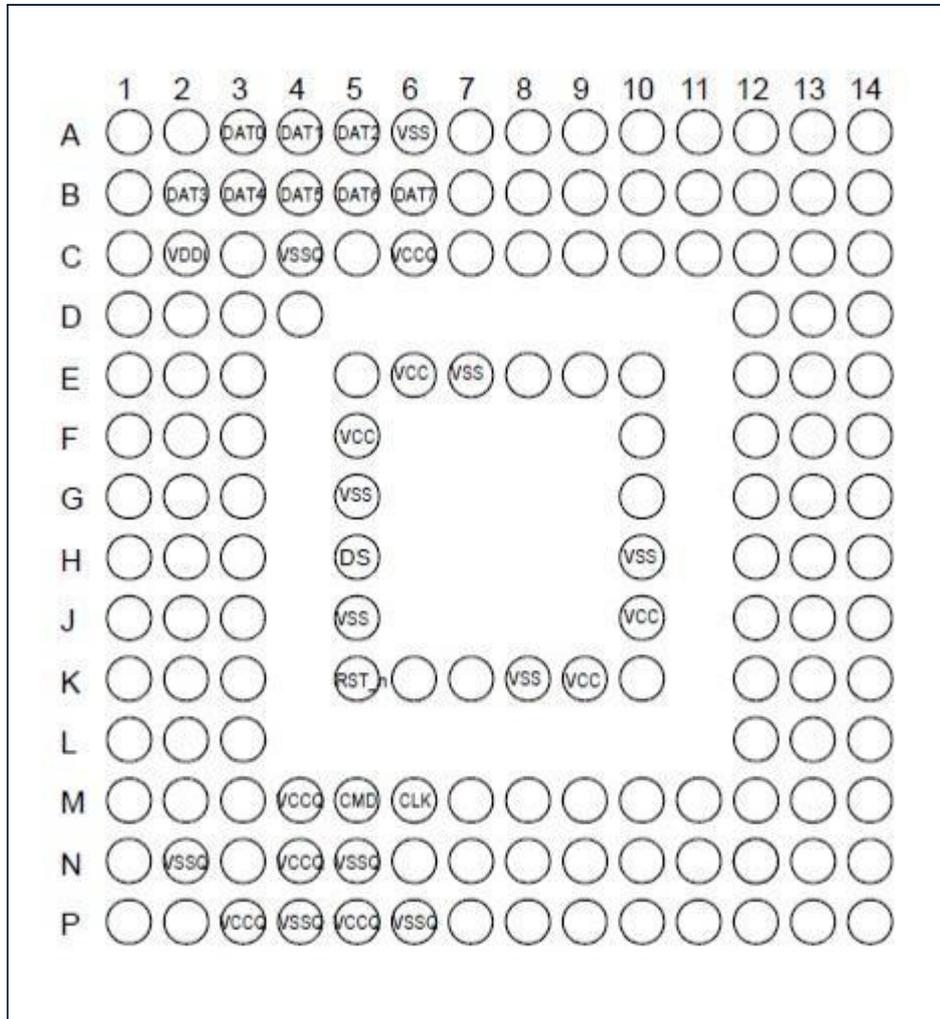
Figure 4-1 eMMC 153 ball pin assignment (Top view)

4.2. eMMC Pin Description

Pin Name	Direction	Description	Pin Number
CLK	I	eMMC clock input	M6
CMD	I/O	eMMC command line	M5
DAT0	I/O	eMMC data line	A3
DAT1			A4
DAT2			A5
DAT3			B2
DAT4			B3
DAT5			B4
DAT6			B5
DAT7			B6
RST_n	I	eMMC reset input	K5
DS	O	eMMC data strobe output	H5
VDDi	Power out	Power supply for core	C2
VCCQ	Power in	Power supply for controller and IO pad	C6, M4, N4, P3, P5
VSSQ	Ground	Ground for controller and IO pad	C4, N2, N5, P4, P6
VCC	Power in	Power supply for NAND flash device	E6, F5, J10, K9
VSS	Ground	Ground for NAND flash device	A6, E7, G5, H10, J5, K8

Table 4-2 eMMC Pin Description

5. Electrical Characteristics

The eMMC is used to provide an interface between on-chip bus and external (off-chip) memory devices.

5.1. General operating conditions

Parameter	Symbol	Min.	Max.	Unit	Remark
Peak voltage on all lines	-	-0.5	V_{CCQ}+0.5	V	
All Inputs					
Input leakage current (before initialization)	-	-100	100	µA	
Input leakage current (after initialization)	-	-2	2	µA	
All Outputs					
Output leakage current (before initialization)	-	-100	100	µA	
Output leakage current (after initialization)	-	-2	2	µA	

Table 5-1 General Operating Conditions

5.2. Power supply voltage

Parameter	Symbol	Min.	Max.	Unit	Remark
Supply voltage (NAND)	V_{CC}	2.7	3.6	V	
Supply voltage (I/O)	V_{CCQ}	2.7	3.6	V	
		1.7	1.95		

Table 5-2 Power Supply Voltage

5.3. Bus Signal Line Loading

Parameter	Symbol	Min.	Max.	Unit	Remark
Pull up resistance for CMD	R_{CMD}	4.7	100[1]	KΩ	
Pull up resistance for DAT0-DAT7	R_{DAT}	10	100[1]	KΩ	
Internal pull up resistance for DAT1-DAT7	R_{int}	10	150	KΩ	
Bus signal line capacitance	C_L	-	30	pF	
Signal device capacitance	C_{Device}	-	6	pF	
Maximum signal line inductance	-	-	16	nH	

Table 5-3 Bus Signal Line Loading

(1) Recommended maximum value is 50 KΩ for 1.8V interface supply voltages. 3V part, may use the whole range up to 100 KΩ.

Parameter	Symbol	Min.	Max.	Unit	Remark
Pull up resistance for CMD	R_{CMD}	4.7	100[1]	KΩ	
Pull up resistance for DAT0-DAT7	R_{DAT}	10	100[1]	KΩ	
Pull down resistance for Data Strobe	R_{DS}	10	100[1]	KΩ	
Internal pull up resistance for DAT1-DAT7	R_{int}	10	150	KΩ	
Signal device capacitance	C_{Device}	-	6	pF	

Table 5-4 Bus Signal Line Loading for HS400

(1) Recommended maximum value is 50 KΩ for 1.8V interface supply voltages.

5.4. Bus Signal Level
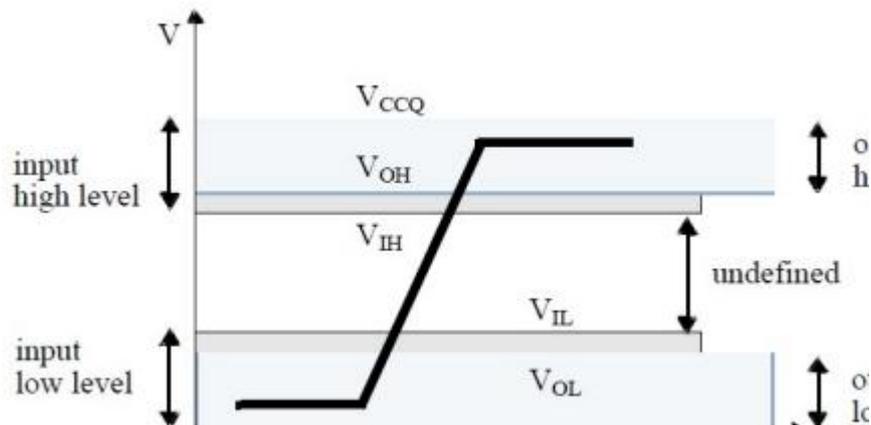
Figure 5-1 Bus Signal Level

Parameter	Symbol	Min.	Max.	Unit	Remark
Output HIGH voltage	V_{OH}	$0.75*V_{CCQ}$	-	V	V_{CCQ} = 3.3V
Output LOW voltage	V_{OL}	-	$0.125*V_{CCQ}$	V	V_{CCQ} = 3.3V
Input HIGH voltage	V_{IH}	$0.625*V_{CCQ}$	$V_{CCQ} + 0.3$	V	V_{CCQ} = 3.3V
Input LOW voltage	V_{IL}	$V_{SS} - 0.3$	$0.25*V_{CCQ}$	V	V_{CCQ} = 3.3V
Output HIGH voltage	V_{OH}	$V_{CCQ} - 0.45$	-	V	VCCQ = 1.8V
Output LOW voltage	V_{OL}	-	0.45	V	V_{CCQ} = 1.8V
Input HIGH voltage	V_{IH}	$0.65*V_{CCQ}$	$V_{CCQ} + 0.3$	V	V_{CCQ} = 1.8V
Input LOW voltage	V_{IL}	$V_{SS} - 0.3$	$0.35*V_{CCQ}$	V	V_{CCQ} = 1.8V

Table 5-5 Bus Signal Level

5.5. Bus Timing for eMMC in backward-compatible device and high speed mode
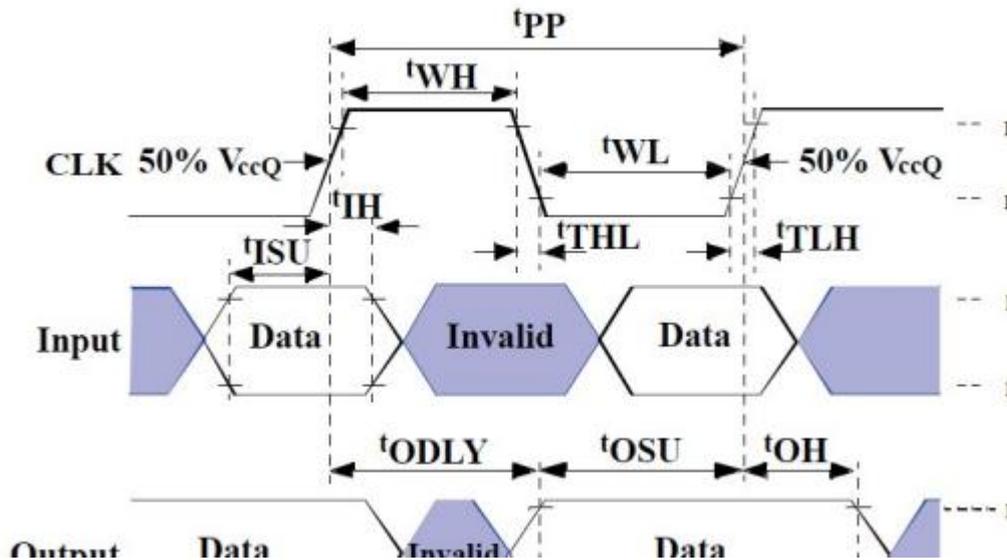
Figure 5-2 Timing diagram data input/output referenced to clock (eMMC in backward-compatible device and high speed)

Parameter	Symbol	Min.	Max.	Unit	Remark
Input MMC_CLK					
Clock frequency data transfer mode	f_{PP}	0	26	MHz	$C_L \leq 30pF$
Clock frequency identification mode	f_{OD}	0	400	KHz	
Clock low time / Clock high time	t_{WL}/t_{WH}	10	-	ns	$C_L \leq 30pF$
Clock rise time / Clock fall time	t_{TLH}/t_{THL}	-	10	ns	$C_L \leq 30pF$
Input MMC_CMD, MMC_DAT (referenced to MMC_CLK)					
Input set-up time	t_{ISU}	3	-	ns	$C_L \leq 30pF$
Input hold time	t_{IH}	3	-	ns	$C_L \leq 30pF$
Output MMC_CMD, MMC_DAT (referenced to MMC_CLK)					
Output set-up time	t_{OSU}	11.7	-	ns	$C_L \leq 30pF$
Output hold time	t_{OH}	8.3	-	ns	$C_L \leq 30pF$

Table 5-6 backward-compatible device mode timing for eMMC

(1) Clock timing is measured at 50% of V_{CCQ}.

(2) Clock rise and fall times are measured by min (V_{IH}) and max (V_{IL}).

Parameter	Symbol	Min.	Max.	Unit	Remark
Input MMC_CLK					
Clock frequency data transfer mode	f_{PP}	0	52	MHz	$C_L \leq 30pF$
Clock frequency identification mode	f_{OD}	0	400	KHz	
Clock low time / Clock high time	t_{WL}/t_{WH}	6.5	-	ns	$C_L \leq 30pF$
Clock rise time / Clock fall time	t_{TLH}/t_{THL}	-	3	ns	$C_L \leq 30pF$
Input MMC_CMD, MMC_DAT (referenced to MMC_CLK)					
Input set-up time	t_{ISU}	3	-	ns	$C_L \leq 30pF$
Input hold time	t_{IH}	3	-	ns	$C_L \leq 30pF$
Output MMC_CMD, MMC_DAT (referenced to MMC_CLK)					
Output delay time during data transfer	t_{ODLY}	-	13.7	ns	$C_L \leq 30pF$
Output hold time	t_{OH}	2.5	-	ns	$C_L \leq 30pF$
Signal rise time	t_{RISE}	-	3	ns	$C_L \leq 30pF$
Signal fall time	t_{FALL}	-	3	ns	$C_L \leq 30pF$

Table 5-7 High speed mode timing for eMMC

(1) Clock timing is measured at 50% of V_{CCQ}.

(2) Clock rise and fall times are measured by min (V_{IH}) and max (V_{IL}).

(3) Inputs CMD, DAT rise and fall times are measured by min (V_{IH}) and max (V_{IL}), and outputs CMD, DAT rise and fall times are measured by min (V_{OH}) and max (V_{OL}).

5.6. Bus Timing for eMMC in DDR Mode
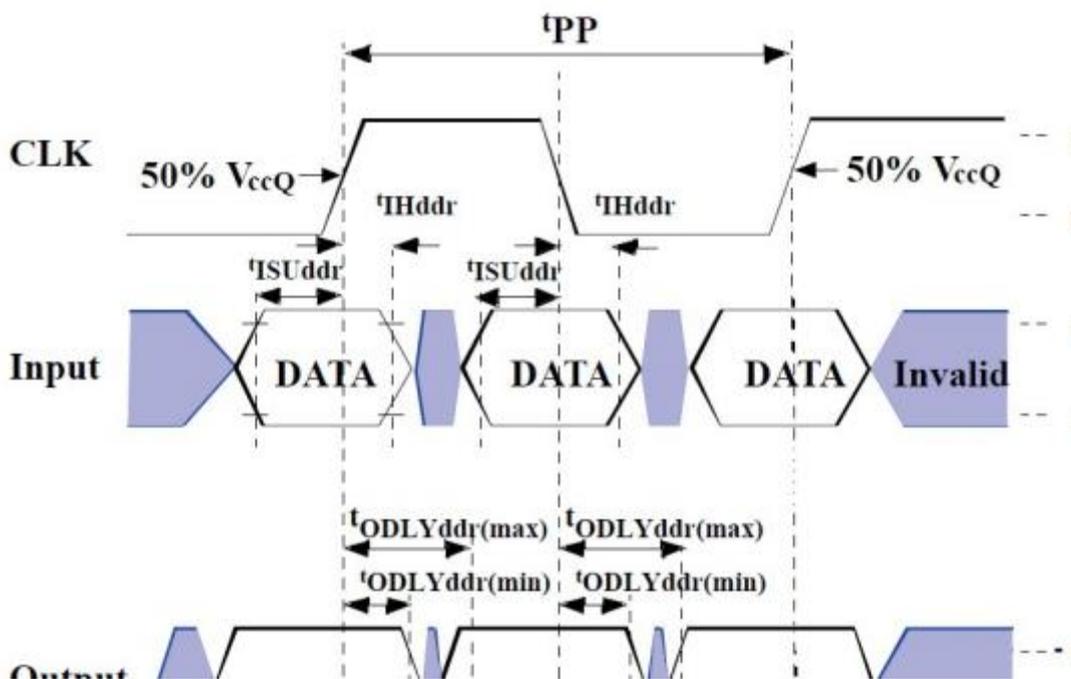
Figure 5-3 Timing diagram data input/output referenced to clock (DDR mode)

Parameter	Symbol	Min.	Max.	Unit	Remark
Input MMC_CLK					
Clock duty cycle	-	45	55	%	
Clock rise time / Clock fall time	t_{TLH}/t_{THL}	-	3	ns	$C_L \leq 30pF$
Input MMC_CMD (referenced to MMC_CLK)					
Input set-up time	t_{ISUddr}	3	-	ns	$C_L \leq 20pF$
Input hold time	t_{IHddr}	3	-	ns	$C_L \leq 20pF$
Output MMC_CMD (referenced to MMC_CLK)					
Output delay time during data transfer	t_{ODLY}	-	13.7	ns	$C_L \leq 20pF$
Output hold time	t_{OH}	2.5	-	ns	$C_L \leq 20pF$
Signal rise time	t_{RISE}	-	3	ns	$C_L \leq 20pF$
Signal fall time	t_{FALL}	-	3	ns	$C_L \leq 20pF$
Input MMC_DAT (referenced to MMC_CLK)					
Input set-up time	t_{ISUddr}	2.5	-	ns	$C_L \leq 20pF$
Input hold time	t_{IHddr}	2.5	-	ns	$C_L \leq 20pF$
Output MMC_DAT (referenced to MMC_CLK)					
Output delay time during data transfer	$t_{ODLYddr}$	1.5	7	ns	$C_L \leq 20pF$
Signal rise time	t_{RISE}	-	2	ns	$C_L \leq 20pF$
Signal fall time	t_{FALL}	-	2	ns	$C_L \leq 20pF$

Table 5-8 DDR mode timing for eMMC

(1) Clock timing is measured at 50% of V_{CCQ}.

(2) Inputs DAT rise and fall times are measured by min (V_{IH}) and max (V_{IL}), and outputs DAT rise and fall times are measured by min (V_{OH}) and max (V_{OL}).

5.7. Bus Timing for eMMC in HS200 Mode
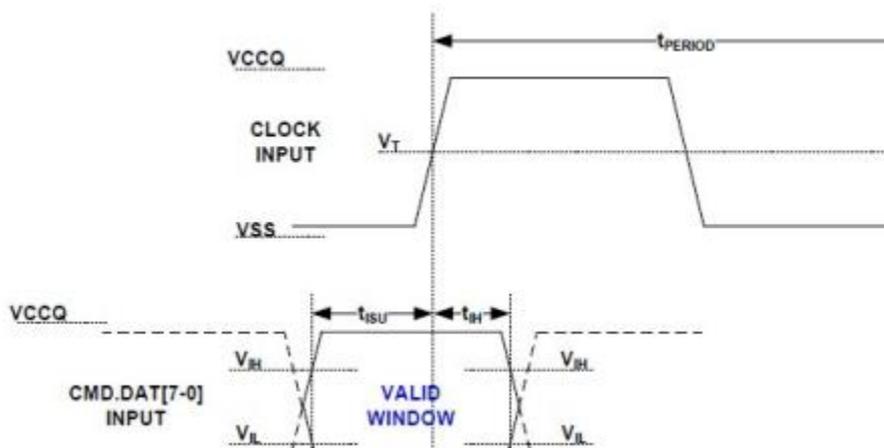
Figure 5-4 Timing diagram data input referenced to clock (HS200 mode)
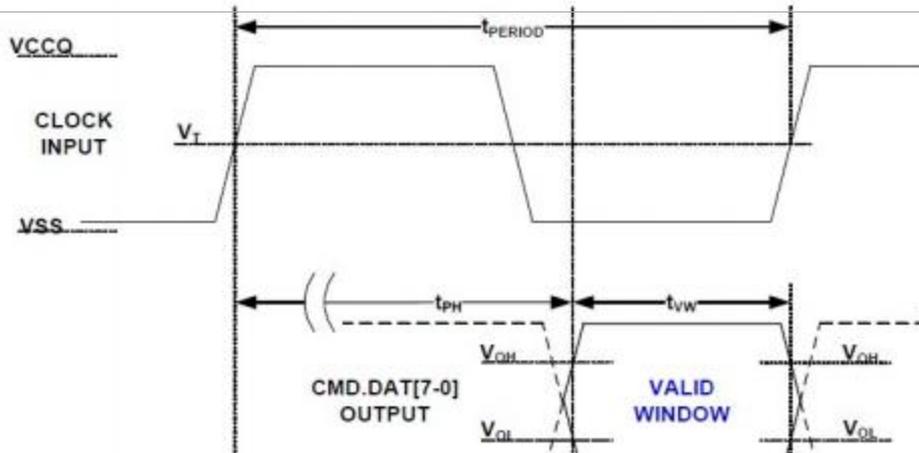
Figure 5-5 Timing diagram data output referenced to clock (HS200 mode)

Parameter	Symbol	Min.	Max.	Unit	Remark
Input MMC_CLK					
Clock cycle time	t_{PERIOD}	5	-	ns	
Clock rise time / Clock fall time	t_{TLH}/t_{THL}	-	1	ns	$C_{Device} = 6$ pF
Clock duty cycle	-	30	70	%	
Input MMC_CMD, MMC_DAT (referenced to MMC_CLK)					
Input set-up time	t_{ISU}	1.4	-	ns	$C_{Device} \leq 6pF$
Input hold time	t_{IH}	0.8	-	ns	$C_{Device} \leq 6pF$
Output MMC_CMD, MMC_DAT (referenced to MMC_CLK)					
Output delay time during data transfer	t_{PH}	0	2	UI	
Delay variation due to temperature change after tuning	ΔTPH	-350 (ΔT=-20。C)	+1550 (ΔT=90。C)	ps	
Output valid data window	t_{VW}	0.575	-	UI	

Table 5-9 HS200 mode timing for eMMC

(1) Unit Interval (UI) is one bit nominal time. For example, UI = 5ns at 200MHz.

5.8. Bus Timing for eMMC in HS400 Mode
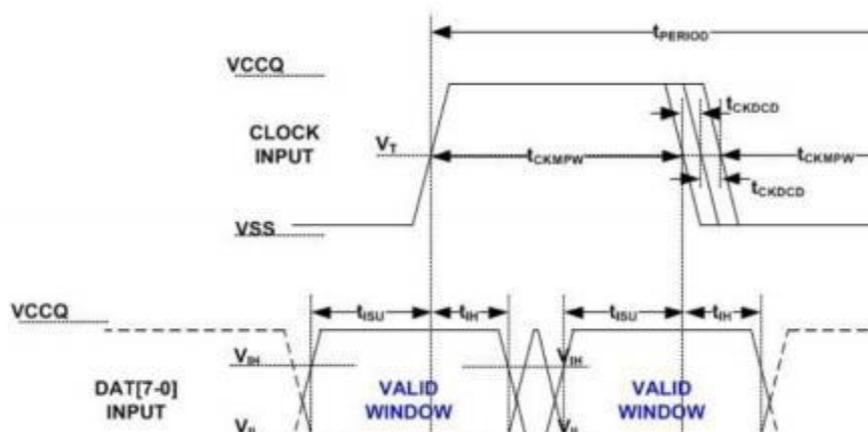
Figure 5-6 Timing diagram data input referenced to clock (HS400 mode)
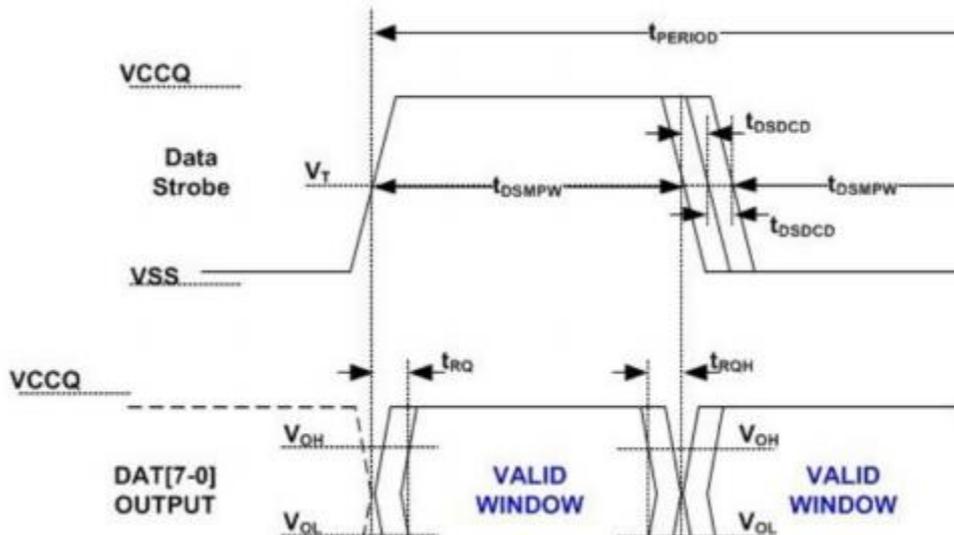
Figure 5-7 Timing diagram data output referenced to clock (HS400 mode)

Parameter	Symbol	Min.	Max.	Unit	Remark
Input MMC_CLK					
Clock cycle time	t_{PERIOD}	5	-	ns	
Slew rate	SR	1.125	-	V/ns	
Duty cycle distortion	t_{CKDCD}	0	0.3	ns	
Minimum pulse width	t_{CKMPW}	2.2	-	ns	
Input MMC_DAT (referenced to MMC_CLK)					
Input set-up time	t_{ISUddr}	0.4	-	ns	$C_{Device} \leq 6pF$
Input hold time	t_{IHddr}	0.4	-	ns	$C_{Device} \leq 6pF$
Slew rate	SR	1.125	-	V/ns	
Output MMC_STRB					
Clock cycle time	t_{PERIOD}	5	-	ns	
Slew rate	SR	1.125	-	V/ns	
Duty cycle distortion	t_{CKDCD}	0	0.2	ns	
Minimum pulse width	t_{CKMPW}	2	-	ns	
Read pre-amble	t_{RPRE}	0.4	-	t_{PERIOD}	
Read post-amble	t_{RPST}	0.4	-	t_{PERIOD}	
Output MMC_ DAT/ MMC_ CMD (referenced to MMC_STRB)					
Output skew	t_{RQ}/t_{RQ_CMD}	-	0.4	ns	
Output holdskew	t_{RQH}/t_{RQH_CMD}	-	0.4	ns	
Slew rate	SR	1.125	-	V/ns	

Table 5-10 HS400 mode timing for eMMC

5.9. Flash Interface AC Characteristic

Parameter	Symbol	Min.	Max.	Unit	Remark
CLE/ALE setup time	t_{CLS}/t_{ALS}	15	-	ns	
CLE/ALE hold time	t_{CLH}/t_{ALH}	5	-	ns	
WE low pulse width	t_{WP}	11	-	ns	
WE high pulse width	t_{WH}	11	-	ns	
RE low pulse width	t_{RP}	2.25	-	ns	
RE high pulse width	t_{REH}	2.25	-	ns	
Read cycle time	t_{RC}	5	-	ns	
Write cycle time	t_{WC}	25	-	ns	
Data setup time	t_{DS}	0.28	-	ns	
Data hold time	t_{DH}	0.28	-	ns	

Table 5-11 Flash Interface AC Characteristic

6. eMMC Register Description

Register Name	eMMC 4.5	eMMC 5.01	eMMC 5.1
Operation Condition Register (OCR)	V	V	V
Card Identification Register (CID)	V	V	V
Driver Stage Register (DSR)	V	V	V
Relative Card Address Register (RCA)	V	V	V
Card Specific Data Register (CSD)	V	V	V
Extended Card Specific Data Register (EXT_CSD)	V	V	V

Table 6-1 eMMC Register table

6.1. Operation Conditions Register (OCR) Register

The 32-bit operation conditions register (OCR) stores the voltage profile of the Device and the access mode indication. In addition, this register includes a status information bit. This status bit is set if the Device power up procedure has been finished.

OCR bit	VCCQ voltage window	eMMC
[6:0]	Reserved	000 0000b
[7]	1.7V~1.95V	1b
[14:8]	2.0V – 2.6V	000 0000b
[23:15]	2.7V – 3.6V	1 1111 1111 b
[28:24]	Reserved	0 0000b
[30:29]	Access Mode	00b (byte mode) 10b (sector mode)
[31]	Card power up status bit (busy)[1]	

Table 6-2 OCR Table

(1) This bit is set to LOW if the Device has not finished the power up routine.

6.2. SD Card Identification Register (CID)

The Device IDentification (CID) register is 128 bits wide. It contains the Device identification information used during the Device identification phase. Every type of eMMC Device shall have a unique identification number. The structure of the CID register is defined in the following table.

CID bit	width	Name	Field
[127:120]	8	Manufacture ID	E7h
[119:114]	6	Reserved	-
[113:112]	2	Device/BGA	01h
[111:104]	8	OEM/Application ID	11h
[103:56]	48	Product Name	PNM
[55:48]	8	Product Revision	01h
[47:16]	32	Product Serial Number	PSN
[15:8]	8	Manufacturing Date	MDT
[7:1]	7	CRC7 check sum	CRC
[0]	1	Not used, always '1'	-

Table 6-3 CID Table

6.3. Driver Stage Register (DSR)

The 16-bit driver stage register (DSR) is optionally used to improve the bus performance for extended operating conditions. The CSD register carries the information about the DSR register usage. The default value of the DSR register is 0x404.

6.4. Relative Card Address Register (RCA)

The writable 16-bit relative Device address (RCA) register carries the Device address assigned by the host during the Device identification. This address is used for the addressed host-Device communication after the Device identification procedure. The default value of the RCA register is 0x0001. The value 0x0000 is reserved to set all Devices into the Stand-by State with CMD7.

6.5. Card Specific Data Register (CSD)

The Device-Specific Data (CSD) register provides information on how to access the Device contents. The CSD defines the data format, error correction type, maximum data access time, data transfer speed, whether the DSR register can be used etc. The programmable part of the register (entries marked by W or E below) can be changed by CMD27.

CSD bit	Width	Name	Field	Type	Value	Note
[127:126]	2	CSD structure	CSD_STRUCTURE	R	3h	
[125:122]	4	System specification version	SPEC_VERS	R	4h	
[121:120]	2	Reserved	-	-	-	-
[119:112]	8	Data read access-time 1	TAAC	R	FFh	
[111:104]	8	Data read access-time 2	NSAC	R	FFh	
[103:96]	8	Max. data transfer rate	TRAN_SPEED	R	32h	25 MHz
[95:84]	12	Device command classes	CCC	R	1F5h	
[83:80]	4	Max. read data block length	READ_BL_LEN	R	9h	512 bytes
[79]	1	Partial block read allowed	READ_BL_PARTIAL	R	0b	Not Support
[78]	1	Write block misalignment	WRITE_BLK_MISALIGN	R	0b	Not Support
[77]	1	Read block misalignment	READ_BLK_MISALIGN	R	0b	Not Support
[76]	1	DSR implemented	DSR_IMP	R	0b	Not support
[75:74]	2	Reserved	-	-	-	-
[73:62]	12	Device size	C_SIZE	R	FFFh	>2GB
[61:59]	3	Max. read current @ VDD min	VDD_R_CURR_MIN	R	3h	
[58:56]	3	Max. read current @ VDD max	VDD_R_CURR_MAX	R	7h	
[55:53]	3	Max. write current @ VDD min	VDD_W_CURR_MIN	R	3h	
[52:50]	3	Max. write current @ VDD max	VDD_W_CURR_MAX	R	7h	
[49:47]	3	Device size multiplier	C_SIZE_MULT	R	7h	
[46:42]	5	Erase group size	ERASE_GRP_SIZE	R	1Fh	
[41:37]	5	Erase group size multiplier	ERASE_GRP_MULT	R	1Fh	
[36:32]	5	Write protect group size	WP_GRP_SIZE	R	1Fh	
[31]	1	Write protect group enable	WP_GRP_ENABLE	R	1b	
[30:29]	2	Manufacturer default ECC	DEFAULT_ECC	R	0h	

CSD bit	Width	Name	Field	Type	Value	Note
[28:26]	3	Write speed factor	R2W_FACTOR	R	2h	4X
[25:22]	4	Max. write data block length	WRITE_BL_LEN	R	9h	512 bytes
[21]	1	Partial block write allowed	WRITE_BL_PARTIAL	R	0b	Not Support
[20:17]	4	Reserved	-	-	-	-
[16]	1	Content protection application	CONTENT_PROT_APP	R	0b	
[15]	1	File format group	FILE_FORMAT_GRP	R/W	0b	HD like FAT
[14]	1	Copy flag (OTP)	COPY	R/W	0b	Not copied
[13]	1	Permanent write protection	PERM_WRITE_PROTECT	R/W	0b	Not protected
[12]	1	Temporary write protection	TMP_WRITE_PROTECT	R/W/E	0b	Not protected
[11:10]	2	File format	FILE_FORMAT	R/W	0h	HD like FAT
[9:8]	2	ECC code	ECC	R/W/E	0h	None
[7:1]	7	CRC	CRC	R/W/E	-	-
[0]	1	Not used, always '1'	-		1b	-

Table 6-4 CSD Table

6.6. Extended CSD register

The Extended CSD register defines the Device properties and selected modes. It is 512 bytes long. The most significant 320 bytes are the Properties segment, that defines the Device capabilities and cannot be modified by the host. The lower 192 bytes are the Modes segment, that defines the configuration the Device is working in. These modes can be changed by the host by means of the SWITCH command.

Extend CSD bit	Width	Name	Field	Type	Value	Note
			Properties Segment			
[511:506]	6	Reserved	-	-	-	-
[505]	1	Extend Security Command Error	EXT_SECURITAY	R	0h	
[504]	1	Supported Command Sets	S_CMD_SET	R	1h	
[503]	1	HPI features	HPI_FEATURES	R	1h	

Extend CSD bit	Width	Name	Field	Type	Value	Note
[502]	1	Background operations support	BKOPS_SUPPORT	R	1h	
[501]	1	Max packed read commands	MAX_PACKED_R EADS	R	3Fh	
[500]	1	Max packed write commands	MAX_PACKED_W RITES	R	3Fh	
[499]	1	Data Tag Support	DATA_TAG_SUP P ORT	R	1h	
[498]	1	Tag Unit Size	TAG_UNIT_SIZE	R	3h	
[497]	1	Tag Resources Size	TAG_RES_SIZE	R	0h	
[496]	1	Context management capabilities	CONTEXT_CAP A BILITIES	R	5h	
[495]	1	Large Unit size	LARGE_UNIT_SI Z E_M1	R	Bh	
[494]	1	Extended partitions attribute support	EXT_SUPPORT	R	3h	
[493]	1	Supported modes	SUPPORTED_MO DES	R	1h	
[492]	1	FFU features	FFU_FEATURES	R	0h	
[491]	1	Operation codes timeout	OPERATION_COD E_TIMEOUT	R	0h	
[490:487]	4	FFU Argument	FFU_ARG	R	6C6F 5341 h	
[486]	1	Barrier support	BARRIER_SUPP O RT	R	0h	
[485:309]	177	Reserved	-	-	-	-
[308]	1	CMD Queuing Support	CMDQ_SUPPORT	R	1h	
[307]	1	CMD Queuing Depth	CMDQ_DEPTH	R	1Fh	
[306]	1	Reserved	-	-	-	-

Extend CSD bit	Width	Name	Field	Type	Value	Note
[305:302]	4	Number of FW sectors correctly programmed	NUMBER_OF_FW_SECTORS_CORRECTLY_PROGRAMMED	R	0h	
[301:270]	32	Vendor proprietary health report	VENDOR_PROPRIETARY_HEALTH_REPORT	R	0h	
[269]	1	Device life time estimation type B	DEVICE_LIFE_TIME_EST_TYP_B	R	1h	
[268]	1	Device life time estimation type A	DEVICE_LIFE_TIME_EST_TYP_A	R	1h	
[267]	1	Pre EOL information	PRE_EOL_INFO	R	1h	
[266]	1	Optimal read size	OPTIMAL_READ_SIZE	R	8h	
[265]	1	Optimal write size	OPTIMAL_WRITE_SIZE	R	8h	
[264]	1	Optimal trim unit size	OPTIMAL_TRIM_UNIT_SIZE	R	4h	
[263:262]	2	Device version	DEVICE_VERSION	R	-	Depend on FW setting
[261:254]	8	Firmware version	FIRMWARE_VERSION	R	-	Depend on FW setting
[253]	1	Power class for 200MHz, DDR at VCC= 3.6V	PWR_CL_DDR_200_360	R	0h	
[252:249]	4	Cache size	CACHE_SIZE	R	400h	128KB
[248]	1	Generic CMD6 timeout	GENERIC_CMD6_TIME	R	Ah	
[247]	1	Power off notification(long) timeout	POWER_OFF_LONG_TIME	R	64h	
[246]	1	Background operations status	BKOPS_STATUS	R	0h	

Extend CSD bit	Width	Name	Field	Type	Value	Note
[245:242]	4	Number of correctly programmed sectors	CORRECTLY_PRG _SECTORS_NUM	R	0h	
[241]	1	Number of correctly programmed sectors	INI_TIMEOUT_AP	R	1Eh	
[240]	1	Cache Flushing Policy	CACHE_FLUSH_P OLICY	R	1h	
[239]	1	Power class for 52MHz, DDR at VCC = 3.6V	PWR_CL_DDR_52 _360	R	0h	
[238]	1	Power class for 52MHz, DDR at VCC = 1.95V	PWR_CL_DDR_52 _ 195	R	0h	
[237]	1	Power class for 200MHz at VCCQ =1.95V, VCC = 3.6V	PWR_CL_200_ 195	R	0h	
[236]	1	Power class for 200MHz, at VCCQ =1.3V, VCC = 3.6V	PWR_CL_200_ 130	R	0h	
[235]	1	Minimum Write Performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_ W_8_52	R	0h	
[234]	1	Minimum Read Performance for 8bit at 52MHz in DDR mode	MIN_PERF_DDR_ R_8_52	R	0h	
[233]	1	Reserved	-	-	-	-
[232]	1	TRIM Multiplier	TRIM_MULT	R	2h	

Extend CSD bit	Width	Name	Field	Type	Value	Note
[231]	1	Secure Feature support	SEC_FEATURE_S UPPORT	R	55h	
[230]	1	Secure Erase Multiplier	SEC_ERASE_MU L T	R	F0h	
[229]	1	Secure TRIM Multiplier	SEC_TRIM_MULT	R	F0h	
[228]	1	Boot information	BOOT_INFO	R	7h	
[227]	1	Reserved	-	-	-	-
[226]	1	Boot partition size	BOOT_SIZE_MUL T	R	20h	
[225]	1	Access size	ACC_SIZE	R	7h	
[224]	1	High-capacity erase unit size	HC_ERASE_GRP _ SIZE	R	1h	
[223]	1	High-capacity erase timeout	ERASE_TIMEOU T _MULT	R	Ah	
[222]	1	Reliable write sector count	REL_WR_SEC_C	R	1h	
[221]	1	High-capacity write protect group size	HC_WP_GRP_SI Z E	R	20h	
[220]	1	Sleep current (VCC)	S_C_VCC	R	7h	
[219]	1	Sleep current (VCCQ)	S_C_VCCQ	R	7h	
[218]	1	Production state awareness timeout	PRODUCTION_ST ATE_AWARENES S_TIMOUT	R	Dh	
[217]	1	Sleep/awake timeout	S_A_TIMEOUT	R	17h	
[216]	1	Sleep Notification Timeout	SLEEP_NOTIFIC A TION_TIME	R	7h	
[215:212]	4	Sector Count	SEC_COUNT	R	-	Depend on eMMC size

Extend CSD bit	Width	Name	Field	Type	Value	Note
[211]	1	Secure Write Protect Information	SECURE_WP_INF O	R	0h	
[210]	1	Minimum Write Performance for 8bit at 52 MHz	MIN_PERF_W_8_ 5 2	R	0h	
[209]	1	Minimum Read Performance for 8bit at 52 MHz	MIN_PERF_R_8_ 5 2	R	0h	
[208]	1	Minimum Write Performance for 8bit at 26 MHz, for 4bit at 52MHz	MIN_PERF_W_8_ 2 6_4_52	R	0h	
[207]	1	Minimum Read Performance for 8bit at 26 MHz, for 4bit at 52MHz	MIN_PERF_R_8_ 2 6_4_52	R	0h	
[206]	1	Minimum Write Performance for 4bit at 26 MHz	MIN_PERF_W_4_ 2 6	R	0h	
[205]	1	Minimum Read Performance for 4bit at 26 MHz	MIN_PERF_R_4_ 2 6	R	0h	
[204]	1	Reserved	-	-	-	-
[203]	1	Power class for 26 MHz at 3.6 V 1 R	PWR_CL_26_360	R	0h	
[202]	1	Power class for 52 MHz at 3.6 V 1 R	PWR_CL_52_360	R	0h	
[201]	1	Power class for 26 MHz at 1.95 V 1 R	PWR_CL_26_195	R	0h	

Extend CSD bit	Width	Name	Field	Type	Value	Note
[200]	1	Power class for 52 MHz at 1.95 V 1 R	PWR_CL_52_ 195	R	0h	
[199]	1	Partition switching timing	PARTITION_SWIT CH_TIME	R	1h	
[198]	1	Out-of-interrupt busy timing	OUT_OF_INTERR UPT_TIME	R	19h	
[197]	1	I/O Driver Strength	DRIVER_STREN G TH	R	1Fh	
[196]	1	Device type	DEVICE_TYPE	R	57h	
[195]	1	Reserved	-	-	-	-
[194]	1	CSD STRUCTURE	CSD_STRUCTURE	R	2h	
[193]	1	Reserved	-	-	-	-
[192]	1	Extended CSD revision	EXT_CSD_REV	R	8h	
Modes Segment						
[191]	1	Command set	CMD_SET	R/W/ E_P	0h	
[190]	1	Reserved	-	-	-	-
[189]	1	Command set revision	CMD_SET_REV	R	0h	
[188]	1	Reserved	-	-	-	-
[187]	1	Power class	POWER_CLASS	R/W/ E_P	0h	
[186]	1	Reserved	-	-	-	-
[185]	1	High-speed interface timing	HS_TIMING	R/W/ E_P	0h	
[184]	1	Strobe Support	STROBE_SUPPO R T	R	1h	
[183]	1	Bus width mode	BUS_WIDTH	W/E_ P	0h	
[182]	1	Reserved	-	-	-	-
[181]	1	Erased memory content	ERASED_MEM_ C ONT	R	0h	
[180]	1	Reserved	-	-	-	-

Extend CSD bit	Width	Name	Field	Type	Value	Note
[179]	1	Partition configuration	PARTITION_CON FIG	R/W/ E & R/W/ E_P	0h	
[178]	1	Boot config protection	BOOT_CONFIG_P ROT	R/W & R/W/ C_P	0h	
[177]	1	Boot bus Conditions	BOOT_BUS_CO N DITIONS	R/W/ E	0h	
[176]	1	Reserved	-	-	-	-
[175]	1	High-density erase group definition	ERASE_GROUP_ D EF	R/W/ E_P	0h	
[174]	1	Boot write protection status registers	BOOT_WP_STA T US	R	0h	
[173]	1	Boot area write protection register	BOOT_WP	R/W & R/W/ C_P	0h	
[172]	1	Reserved	-	-	-	-
[171]	1	User area write protection register	USER_WP	R/W, R/W/ C_P & R/W/ E_P	0h	
[170]	1	Reserved	-	-	-	-
[169]	1	FW configuration	FW_CONFIG	R/W	0h	
[168]	1	RPMB Size	RPMB_SIZE_MUL T	R	20h	
[167]	1	Write reliability setting register	WR_REL_SET	R/W	1Fh	
[166]	1	Write reliability parameter register	WR_REL_PARAM	R	15h	

Extend CSD bit	Width	Name	Field	Type	Value	Note
[165]	1	Start Sanitize operation	SANITIZE_START	W/E_P	0h	
[164]	1	Manually start background operations	BKOPS_START	W/E_P	0h	
[163]	1	Enable background operations handshake	BKOPS_EN	R/W & R/W/E	0h	
[162]	1	H/W reset function	RST_n_FUNCTION	R/W	0h	
[161]	1	HPI management	HPI_MGMT	R/W/E_P	0h	
[160]	1	Partitioning Support	PARTITIONING_SUPPORT	R	7h	
[159:157]	3	Max Enhanced Area Size	MAX_ENH_SIZE_ MULT	R	-	Depend on flash and FW setting
[156]	1	Partitions attribute	PARTITIONS_ATTRIBUTE	R/W	0h	
[155]	1	Partitioning Setting	PARTITION_SETTING_COMPLETED	R/W	0h	
[154:143]	12	General Purpose Partition Size	GP_SIZE_MULT	R/W	0h	
[142:140]	3	Enhanced User Data Area Size	ENH_SIZE_MULT	R/W	0h	
[139:136]	4	Enhanced User Data Start Address	ENH_START_ADD R	R/W	0h	
[135]	1	Reserved	-	-	-	-
[134]	1	Bad Block Management mode	SEC_BAD_BLK_ M GMNT	R/W	0h	
[133]	1	Production state awareness	PRODUCTION_STATE_AWARENESS	R/W/E	0h	

Extend CSD bit	Width	Name	Field	Type	Value	Note
[132]	1	Package Case Temperature is controlled	TCASE_SUPPORT	W/E–P	0h	
[131]	1	Periodic Wake-up	PERIODIC_WAKE UP	R/W/E	0h	
[130]	1	Program CID/CSD in DDR mode support	PROGRAM_CID_C SD_DDR_SUPPOR T	R	1h	
[129:128]	2	Reserved	-	-	-	-
[127:64]	64	Vendor Specific Fields	VENDOR_SPECIF I C_FIELD	R	-	Depend on FW settin g
[63]	1	Native sector size	NATIVE_SECTO R _SIZE	R	0h	
[62]	1	Sector size emulation	USE_NATIVE_S E CTOR	R/W	0h	
[61]	1	Sector size	DATA_SECTOR_ S IZE	R	0h	
[60]	1	1st initialization after disabling sector size emulation	INI_TIMEOUT_EM U	R	0h	
[59]	1	Class 6 commands control	CLASS_6_CTRL	R/W/E_P	0h	
[58]	1	Number of addressed group to be Released	DYNCAP_NEED E D	R	0h	
[57:56]	2	Exception events control	EXCEPTION_EV E NTS_CTRL	R/W/E_P	0h	
[55:54]	1	Exception events status	EXCEPTION_EV E NTS_STATUS	R	0h	

Extend CSD bit	Width	Name	Field	Type	Value	Note
[53:52]	2	Extended Partitions Attribute	EXT_PARTITIONS _ATTRIBUTE	R/W	0h	
[51:37]	15	Context configuration	CONTEXT_CONF	R/W/ E_P	0h	
[36]	1	Packed command status	PACKED_COMMA ND_STATUS	R	0h	
[35]	1	Packed command failure index	PACKED_FAILUR E_INDEX	R	0h	
[34]	1	Power Off Notification	POWER_OFF_NO T IFICATION	R/W/ E_P	0h	
[33]	1	Control to turn the Cache ON/OFF	CACHE_CTRL	R/W/ E_P	0h	
[32]	1	Flushing of the cache	FLUSH_CACHE	W/E_ P	0h	
[31]	1	Control to turn the Barrier ON/OFF	BARRIER_CTRL	R/W	0h	
[30]	1	Mode config	MODE_CONFIG	R/W/ E_P	0h	
[29]	1	Mode operation codes	MODE_OPERATIO N_CODES	W/E_ P	0h	
[28:27]	2	Reserved	-	-	-	-
[26]	1	FFU status	FFU_STATUS	R	0h	
[25:22]	4	Pre loading data size	PRE_LOADING_D ATA_SIZE	R/W/ E_P	0h	
[21:18]	4	Max pre loading data size	MAX_PRE_LOADI NG_DATA_SIZE	R	12370 0h	
[17]	1	Product state awareness enablemen	PRODUCT_STATE _AWARENESS_E NABLEMENT	R/W/ E & R	0h	
[16]	1	Secure Removal Type	SECURE_REMO V AL_TYPE	R/W & R	9h	
[15]	1	Command Queue Mode Enable	CMDQ_MODE_EN	R/W/ E_P	0h	
[14:0]	1	Reserved	-	-	-	-

Table 6-5 Extend CSD Table

7. Production Specifications

7.1. Performance

Part Number	Capacities	Flash Type	Interleave Operation	Frequency / Mode	Flash I/O	Performance (MB/S)	
						Write	Read
ZDEMDCM016G-84A8	16 GB	256Gb TLCx1	N	200MHz / HS400	1.8 v	151.2	338.60
ZDEMDCM032G-84A8	32 GB	256Gb TLCx1	N	200MHz / HS400	1.8 v	149.3	333.49
ZDEMDCM064G-95A8	64 GB	512Gb TLCx1	N	200MHz / HS400	1.2v	249.15	338.68

Table 7-1 WR performance

7.2. Power Consumption

Operating Current

Part Number	Capacities	Flash Type	Interleave Operation	Frequency / Mode	Flash I/O	Max Operating Current (mA)	
						Write	Read
ZDEMDCM016G-84A8	16 GB	256Gb TLCx1	N	200MHz / HS400	1.8 v	70	68.6
ZDEMDCM032G-84A8	32 GB	256Gb TLCx1	N	200MHz / HS400	1.8 v	77	79.6
ZDEMDCM064G-95A8	64 GB	512Gb TLCx1	N	200MHz / HS400	1.2v	180	200

Table 9-2 Operating Current

8. Partition Management

The embedded device offers also the possibility of configuring by the host additional split local memory partitions with independent addressable space starting from logical address 0x00000000 for different usage models. Default size of each Boot Area Partition is 4096 KB and can be changed by Vendor Command as multiple of 128KB. Boot area partition size is calculated as (128KB * BOOT_SIZE_MULTI) The size of Boot Area Partition 1 and 2 cannot be set independently . Therefore, memory block area scan is classified as follows:

Boot and RPMB Size:

	Boot1 Size	Boot2 Size	RPMB Size
Default	4096 KB	4096 KB	4096 KB
Max.	4096 KB	4096 KB	4096 KB

User Density Size:

| Capacity	User Area Capacity	SEC_Count in Extended CSD
16 GB	15,615,393,792 Bytes (14892 MB)	0x1D1E000
32 GB	7,818,182,656 Bytes (29818 MB)	0x3A3D000
64 GB	15,634,268,160 Bytes (59636 MB)	0x747A000

9. Package Dimension

SYMBOL	DIMENSION IN MM			DIMENSION IN INCH		
	MIN.	NOM	MAX.	MIN.	NOM	MAX.
A	---	---	1.00	---	---	0.039
A1	0.15	---	---	0.006	---	---
A2	---	---	0.71	---	---	0.028
b	0.25	0.30	0.35	0.010	0.012	0.014
D	12.90	13.00	13.10	0.508	0.512	0.516
E	11.40	11.50	11.60	0.449	0.453	0.457
e	0.5 BSC.			0.020 BSC.		
JEDEC	MO-276					
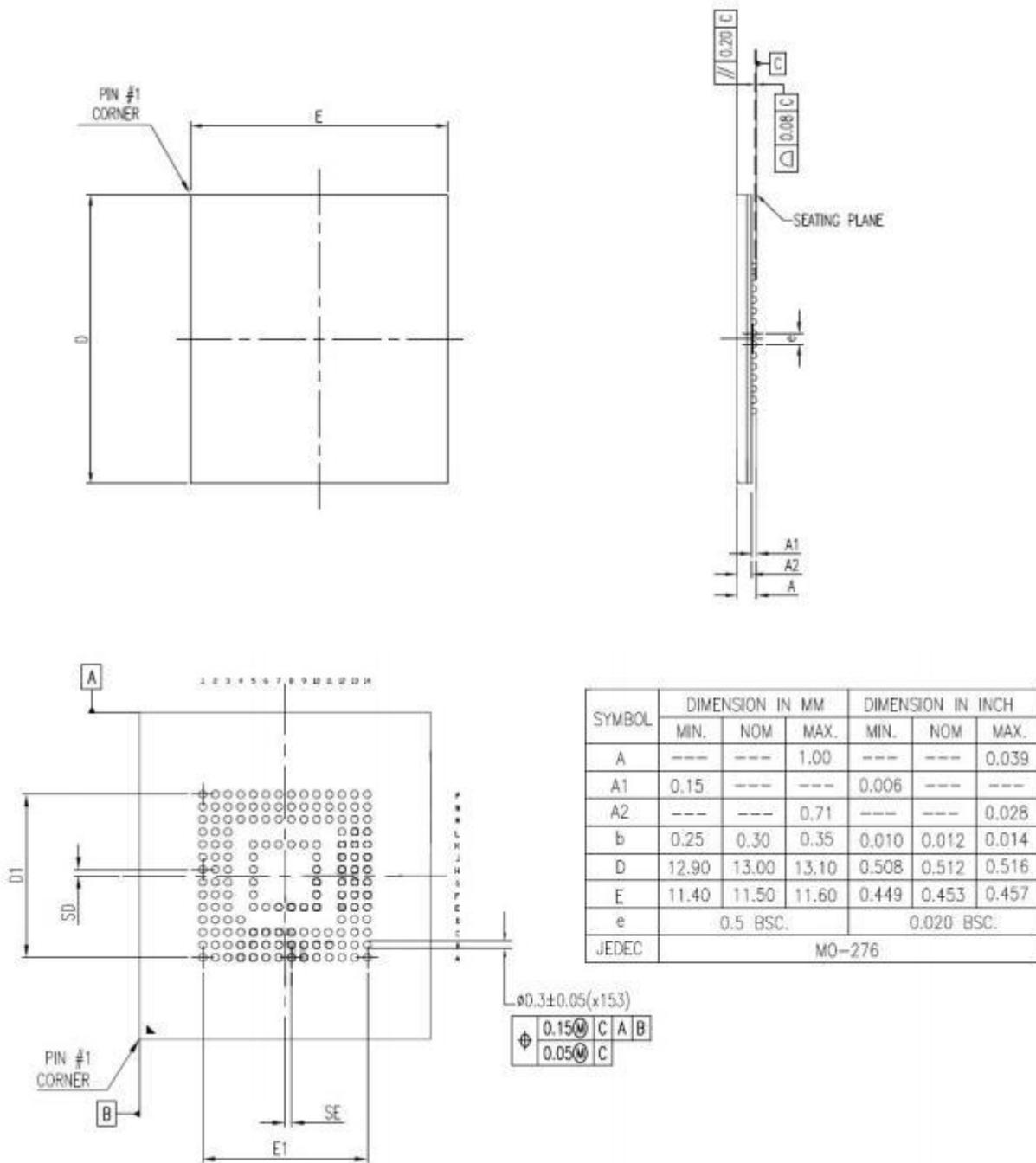
Figure 9-1 Package Outline Dimension Drawing

10. Revision History

Revision	Date	Description
Rev.1.0	2023/08/10	Preliminary version